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## FCB11N60 N-Channel SuperFET<sup>®</sup> MOSFET 600 V, 11 A, 380 mΩ

### Features

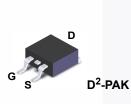
- 650V @ T<sub>J</sub> = 150°C
- Typ. R<sub>DS(on)</sub> = 320 mΩ
- Ultra Low Gate Charge (Typ. Q<sub>g</sub> = 40 nC)
- Low Effective Output Capacitance (Typ. C<sub>oss(eff.)</sub> = 95 pF)
- 100% Avalanche Tested
- RoHS Compliant

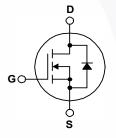
### Application

- Lighting
- Solar Inverter
- AC-DC Power Supply

### Description

SuperFET<sup>®</sup> MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low onresistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.





### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter		Unit
V <sub>DSS</sub>	Drain to Source Voltage		600	V
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)	11	Α
	Drain Current	- Continuous (T <sub>C</sub> = 100 <sup>o</sup> C)	7	
I <sub>DM</sub>	Drain Current	- Pulsed (Note	1) 33	Α
V <sub>GSS</sub>	Gate to Source Voltage	±30	V	
E <sub>AS</sub>	Single Pulsed Avalanche	2) 340	mJ	
I <sub>AR</sub>	Avalanche Current	1) 11.0	Α	
E <sub>AR</sub>	Repetitive Avalanche Ene	1) 12.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		3) 4.5	V/ns
P <sub>D</sub>	Dower Dissinction	(T <sub>C</sub> = 25°C)	125	W
	Power Dissipation	- Derate Above 25°C	1.0	W/ºC
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

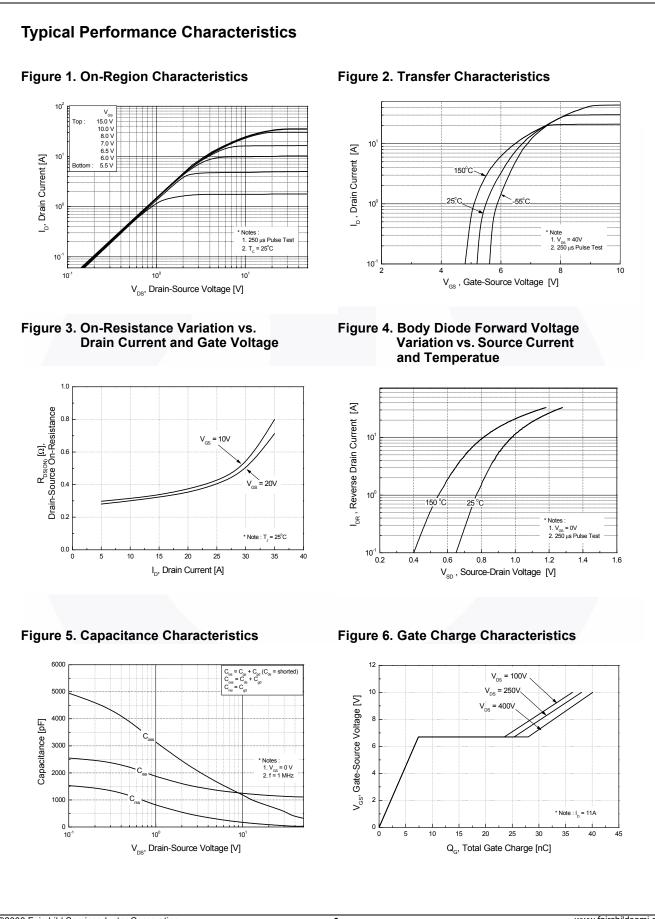
### **Thermal Characteristics**

Symbol	Parameter	FCB11N60TM	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	1.0	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient (1 in <sup>2</sup> Pad of 2-oz Copper), Max.	40	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	

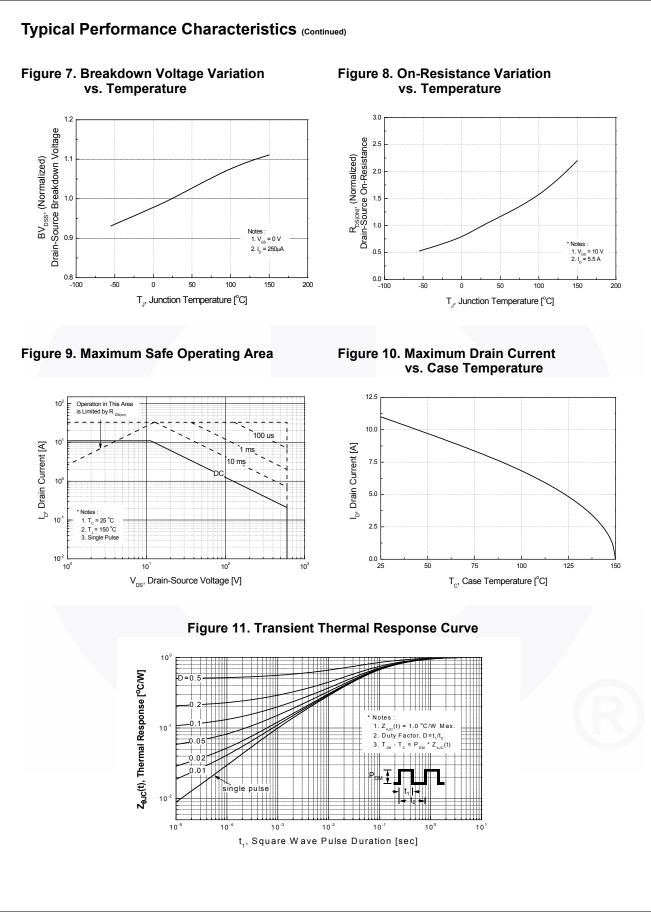
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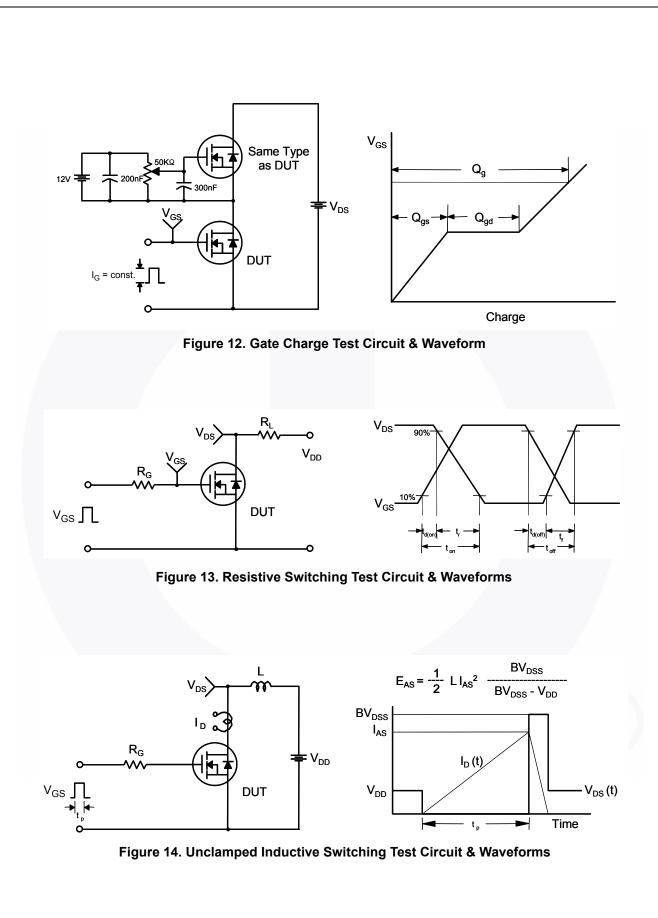
FCB11N60 -
- N-Channel
SuperFET®
MOSFET

Part Nur	•		Package	Packing Method	Reel Size	Тар	e Width	Qua	ntity
FCB11N6			D <sup>2</sup> -PAK			24 mm		800 units	
Electrica	al Char	racteristics T <sub>c</sub> = 25 <sup>c</sup>	C unless	otherwise noted.					
Symbol		Parameter		Test Conditio	ons	Min.	Тур.	Max.	Uni
Off Charac	teristics	6							
D\/	Drain to	Drain to Source Breakdown Voltage		$V_{GS}$ = 0 V,I <sub>D</sub> = 250 µA, T <sub>C</sub> = 25 <sup>o</sup> C		600	-	-	V
BV <sub>DSS</sub>	Dialitito			V <sub>GS</sub> = 0 V,I <sub>D</sub> = 250 μA, T <sub>C</sub> = 150 <sup>o</sup> C		-	650	-	V
ΔΒV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdo Coefficie	own Voltage Temperature ent		$I_D = 250 \ \mu$ A, Referenced to $25^{\circ}$ C		-	0.6	-	V/ºC
BV <sub>DS</sub>	Drain-Source Avalanche Breakdown Voltage		vn	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 11 A		-	700	-	v
I <sub>DSS</sub>	Zero Gate Voltage Drain Current			$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_C = 125^{\circ}\text{C}$		-	-	1	μA
						-	-	10	μΑ
I <sub>GSS</sub>	Gate to	Body Leakage Current		$V_{GS} = \pm 30 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$		-	-	±100	nA
On Charac	teristics	6							
V <sub>GS(th)</sub>	Gate Threshold Voltage			V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA		3.0	-	5.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance			$V_{GS} = 10 \text{ V}, I_D = 5.5 \text{ A}$		-	0.32	0.38	Ω
9 <sub>FS</sub>	Forward Transconductance			V <sub>DS</sub> = 40 V, I <sub>D</sub> = 5.5 A		-	9.7	-	S
Dynamic C	haracte	eristics			¥		J.		
C <sub>iss</sub>	-	apacitance				-	1148	1490	pF
C <sub>oss</sub>	Output C	Output Capacitance		$V_{DS} = 25 V, V_{GS} = 0 V,$		-	671	870	pF
C <sub>rss</sub>	Reverse	Transfer Capacitance		f = 1.0 MHz		-	63	-	pF
C <sub>oss</sub>	Output Capacitance			V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V, f = 1 MHz		-	35	-	pF
C <sub>oss(eff.)</sub>	Effective Output Capacitance			$V_{DS}$ = 0 V to 400 V, $V_{GS}$ = 0 V		-	95	-	pF
Switching	Charact	teristics							
t <sub>d(on)</sub>	Turn-On Delay Time					-	34	80	ns
t <sub>r</sub>	Turn-On Rise Time Turn-Off Delay Time			$V_{DD}$ = 300 V, I <sub>D</sub> = 11 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 25 Ω		-	98	205	ns
t <sub>d(off)</sub>						-	119	250	ns
t <sub>f</sub>	Turn-Off	Fall Time		(Note 4)		-	56	120	ns
Q <sub>g(tot)</sub>	Total Ga	al Gate Charge at 10V		· · · · ·		7 -	40	52	nC
Q <sub>gs</sub>		Source Gate Charge		V <sub>DS</sub> = 480 V, I <sub>D</sub> = 11 A, V <sub>GS</sub> = 10 V		-	7.2	-	nC
Q <sub>gd</sub>	Gate to	Drain "Miller" Charge		00	(Note 4)	-	21	-	nC
	rce Diod	le Characteristics							
I <sub>S</sub>		n Continuous Drain to Sou	rce Diode	Forward Current		-	-	11	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Fo					-	-	33	Α
V <sub>SD</sub>	Drain to Source Diode Forward Voltage		tage	$V_{GS} = 0 \text{ V}, \text{ I}_{SD} = 11 \text{ A}$		-	-	1.4	V
t <sub>rr</sub>		everse Recovery Time		$V_{GS} = 0 V, I_{SD} = 11 A,$		-	390		ns
Q <sub>rr</sub>		Recovery Charge		$dI_F/dt = 100 A/\mu s$		-	5.7		μC
Notes:									<u> </u>



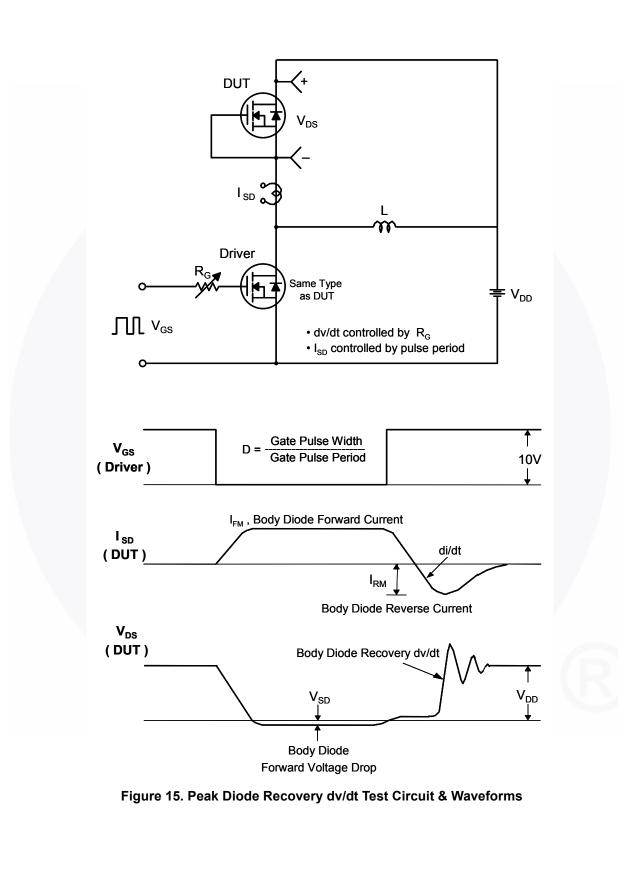
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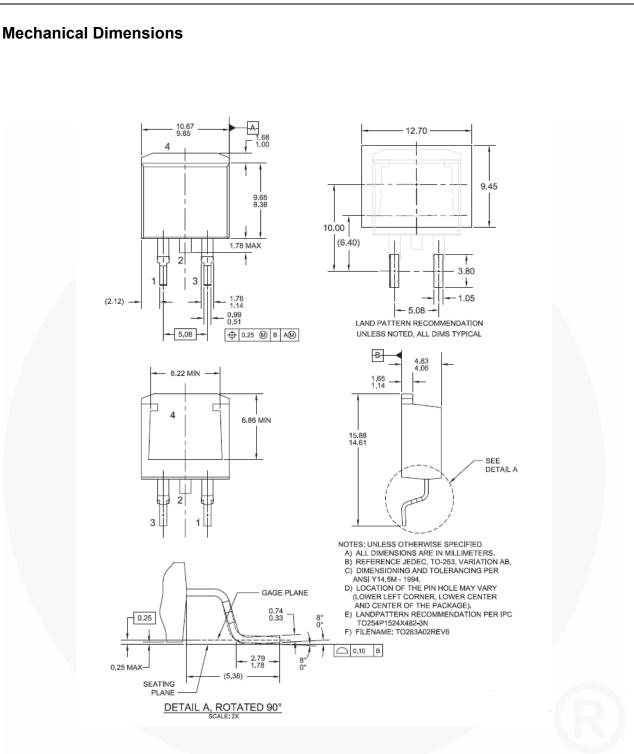




FCB11N60 — N-Channel SuperFET<sup>®</sup> MOSFET

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### Figure 16. TO263 (D<sup>2</sup>PAK), Molded, 2-Lead, Surface Mount

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		PowerTrench <sup>®</sup> PowerXS™ Programmable Active Droop™ QFET <sup>®</sup> QS™ Quiet Series™ RapidConfigure™	SYSTEM <sup>®*</sup> GENERAL TinyBoost <sup>®</sup> TinyBuck <sup>®</sup> TinyCalc <sup>™</sup> TinyLogic <sup>®</sup> TINYOPTO™
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